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Quad. Bus Transceivers (with 3-state outputs)
Quad. Bus Transceivers (with noninverted 3-state outputs)



ADE-205-473 (Z) 1st. Edition Sep. 2000

Description

The HD74HC242 is an inverting buffer and the HD74HC243 is a noninverting buffer. Each device has one active high enable (GBA), and one active low enable ($\overline{G}AB$). GBA enables the A output and $\overline{G}AB$ enables the B outputs. The device does not have schmitt trigger inputs.

Features

• High Speed Operation: $t_{pd} = 10 \text{ ns typ } (C_L = 50 \text{ pF})$

• High Output Current: Fanout of 15 LSTTL Loads

• Wide Operating Voltage: $V_{CC} = 2$ to 6 V

• Low Input Current: 1 μA max

• Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)

Function Table

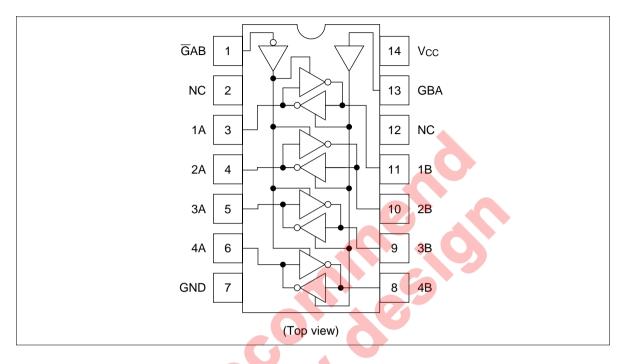
	A 0	HD74HC242		HC74HC243		
Control inputs		Data Port Statu	IS	Data Port Status		
GAB	GBA	A	В	A	В	
Н	Н	Ō	1	0	1	
L	Н	Z	Z	Z	Z	
Н	L	Z	Z	Z	Z	
L	L	1	Ō	1	0	

I : Input
O : Output

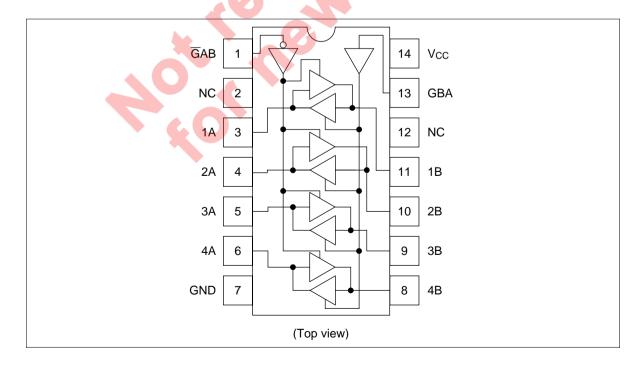
O : Inverting OutputZ : Hight Impedance

Pin Arrangement

HD74HC242



HD74HC243



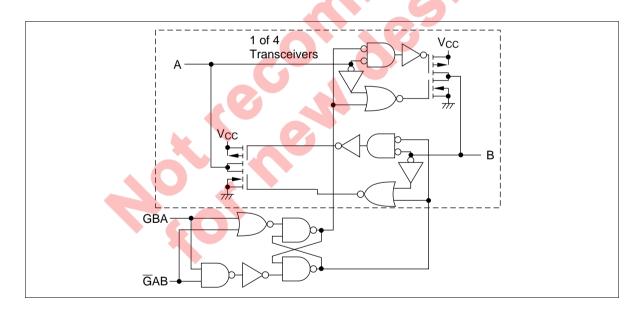
RENESAS

Absolute Maximum Ratings

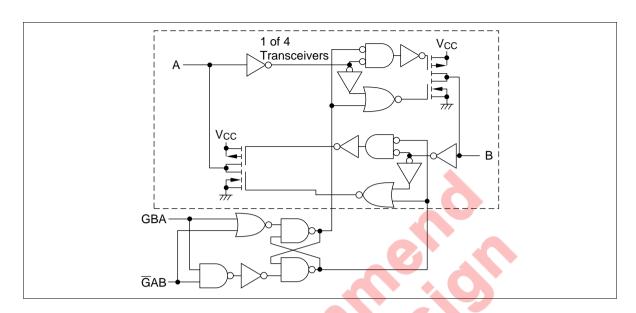
Item	Symbol	Rating	Unit
Supply voltage range	V _{cc}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{\rm CC}$ + 0.5	V
Output voltage	V _{OUT}	-0.5 to V_{CC} + 0.5	V
DC current drain per pin	I _{OUT}	±35	mA
DC current drain per VCC, GND	$I_{\rm CC},I_{\rm GND}$	±75	mA
DC input diode current	I _{IK}	±20	mA
DC output diode current	I _{OK}	±20	mA
Power Dissipation per package	P_{T}	500	mW
Storage temperature	Tstg	-65 to +150	°C

Logic Diagram

HD74HC242



HD74HC243



DC Characteristics

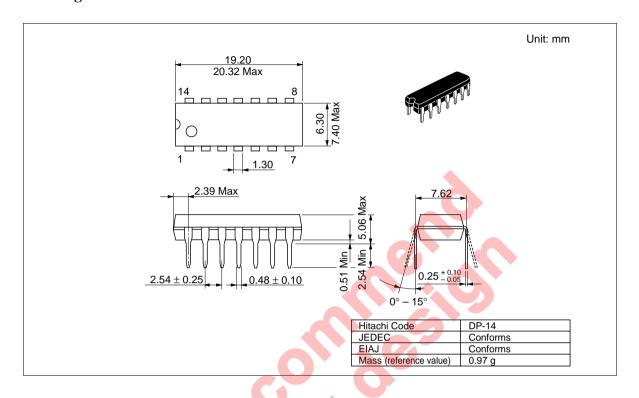
			Ta =	: 25°(;	Ta = - +85°C	-40 to		
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Input voltage	V_{IH}	2.0	1.5	_		1.5	_	V	
		4.5	3.15	_	_	3.15	_		
		6.0	4.2	_	_	4.2	_		
	V _{IL}	2.0	_	_	0.5	_	0.5	V	
		4.5	_	_	1.35	_	1.35		
		6.0	_	_	1.8	_	1.8		
Output voltage	V _{OH}	2.0	1.9	2.0	_	1.9	_	V	Vin = V_{IH} or V_{IL} $I_{OH} = -20 \mu A$
		4.5	4.4	4.5	_	4.4	_		
		6.0	5.9	6.0	_	5.9	- (
		4.5	4.18	_	_	4.13			$I_{OH} = -6 \text{ mA}$
		6.0	5.68	_	_	5.63			$I_{OH} = -7.8 \text{ mA}$
	V _{OL}	2.0	_	0.0	0.1		0.1	V	$Vin = V_{IH} \text{ or } V_{IL} I_{OL} = 20 \mu A$
		4.5	_	0.0	0.1	7	0.1		
		6.0	_	0.0	0.1	_	0.1	9	
		4.5	7	4	0.26	_ (0.33		$I_{OL} = 6 \text{ mA}$
		6.0	-1		0.26		0.33	=	$I_{OL} = 7.8 \text{ mA}$
Off-state output current	I _{oz}	6.0	4	_	±0.5	7	±5.0	μΑ	$Vin = V_{IH} \text{ or } V_{IL},$ $Vout = V_{CC} \text{ or GND}$
Input current	lin	6.0		7	±0.1	_	±1.0	μΑ	Vin = V _{CC} or GND
Quiescent supply current	I _{cc}	6.0	4		4.0	_	40	μА	Vin = V_{cc} or GND, lout = $0 \mu A$

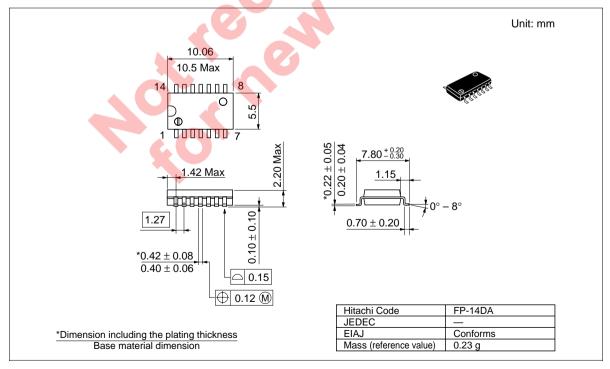
AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Ta = -40 to $Ta = 25^{\circ}C$ +85°C

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Propagation delay	t _{PHL}	2.0	_	_	90	_	115	ns	
time		4.5	_	10	18	_	23		
		6.0	_	_	15	_	20	_	
	t _{PLH}	2.0	_	_	90	_	115	ns	
		4.5	_	10	18	_	23		
		6.0	_	_	15	_	20	_	
Output enable	t _{zL}	2.0	_	_	150	_	190	ns	
time		4.5	_	14	30	_	38		
		6.0	_	_	26	_	33		
	t _{zH}	2.0	_	_	150	_	190	ns	
		4.5	_	15	30	-4	38		(O)
		6.0	_	_	26		33		
Output disable	t _{LZ}	2.0	_	_	150	77	190	ns	
time		4.5	_	18	30	- 1	38	3	
		6.0	_	A	26	- (33		
	t _{HZ}	2.0		رك	150	_ `	190	ns	
		4.5	7	20	30	7	38	=	
		6.0		_	26		33	=	
Output rise/fall	t _{TLH}	2.0	_	4	60	_	75	ns	
time	t _{THL}	4.5	4	4	12	_	15	_	
		6.0	_		10	_	13	_	
Input capacitance	Cin	=	_	5	10		10	pF	

Package Dimensions





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